

In the Claims:

Please add the following new claims:

--38. (NEW) The method of claim 36, wherein the etch point detection window is wider than the actual pattern area.

G4 39. (NEW) The method of claim 36, wherein the gate insulation film is part of a display device having a display part and a non-display part, and in the forming step, the etch point detection window is formed on the non-display part or on a pad portion of the display part.

40. (NEW) The method of claim 36, wherein the predetermined thickness of the dummy pattern represents a desired thickness of the gate insulation film remaining after the etching, at where the etching occurred.

41. (NEW) The method of claim 36, wherein the forming step includes:
forming a gate insulation film on a substrate;
forming an organic protective film on the gate insulation film; and
forming a photoresist pattern on the organic protective film to form the etch point detection window and the actual pattern area.

42. (NEW) The method of claim 41, wherein the simultaneously etching step includes:

placing the substrate having the formed etch point detection window and the actual pattern area, in an etching chamber; and
injecting an etching gas into the etching chamber.

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43. (NEW) The method of claim 36, wherein, in the simultaneously etching step, an etching rate at the etch point detection window and an etching rate at the actual pattern area are the same.

44. (NEW) The method of claim 36, wherein the actual pattern area includes at least one of the following:

an area between two adjacent data links; and

an area between two adjacent gate links.

45. (NEW) The method of claim 37, wherein the reactive gases include non-volatile SiF_4 gas.--
